OptiMOS(TM)3 Power-Transistor

Features

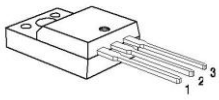
- Ideal for high frequency switching and sync. rec.
- Optimized technology for DC/DC converters
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC[1] for target applications
- Halogen-free according to IEC61249-2-21

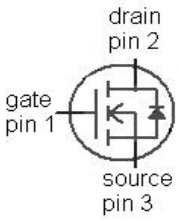
Product Summary

V_{DS}	80	V
$R_{DS(on),max}$	2.8	mΩ
I_D	89	A

RoHS

Halogen-Free

Type	IPA028N08N3 G
	
Package	PG-TO-220-FP
Marking	028N08N



Maximum ratings, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	T_C=25 °C[2]	89	A
		T_C=100 °C	62	
Pulsed drain current[3]	$I_{D,pulse}$	T_C=25 °C	352	
Avalanche energy, single pulse[4]	E_{AS}	I_D=89 A, R_{GS}=25 Ω	1430	mJ
Gate source voltage	V_{GS}		±20	V
Power dissipation	P_{tot}	T_C=25 °C	42	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
IEC climatic category; DIN IEC 68-1			55/175/56	

[1] J-STD20 and JESD22

[2] Current is limited by package; with an R_{thJC}=0.5K/W in a standard TO-220 package the chip is able to carry 251A.

[3] See figure 3 for more detailed information

[4] See figure 13 for more detailed information

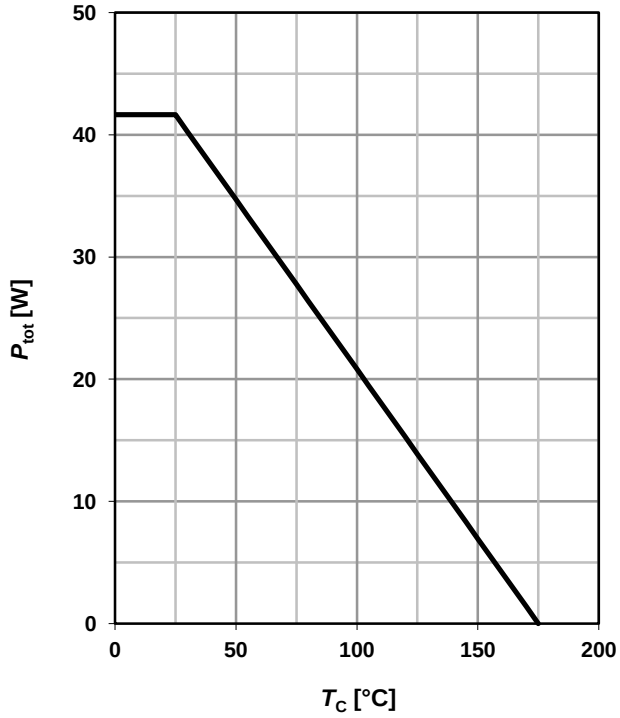
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	3.6	K/W
Electrical characteristics, at T_j=25 °C, unless otherwise specified						
Static characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	V_{GS}=0 V, I_D=1 mA	80	-	-	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=270 µA	2	2.8	3.5	
Zero gate voltage drain current	I_{DSS}	V_{DS}=80 V, V_{GS}=0 V, T_j=25 °C	-	0.1	1	µA
		V_{DS}=80 V, V_{GS}=0 V, T_j=125 °C	-	10	100	
Gate-source leakage current	I_{GSS}	V_{GS}=20 V, V_{DS}=0 V	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=89 A	-	2.4	2.8	mΩ
		V_{GS}=6 V, I_D=44 A	-	2.8	4.2	
Gate resistance	R_G		-	2.7	-	Ω
Transconductance	g_{fs}	$\|V_{DS}\|>2\|I_D\|R_{DS(on)max}$, I_D=89 A	89	178	-	S

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	V_{GS}=0 V, V_{DS}=40 V, f=1 MHz	-	10700	14200	pF
Output capacitance	C_{oss}		-	2890	3840	
Reverse transfer capacitance	C_{rss}		-	100	-	
Turn-on delay time	$t_{d(on)}$	V_{DD}=40 V, V_{GS}=10 V, I_D=89 A, $R_{G,ext}$=1.6 Ω	-	30	-	ns
Rise time	t_r		-	59	-	
Turn-off delay time	$t_{d(off)}$		-	77	-	
Fall time	t_f		-	26	-	
Gate Charge Characteristics[5)]						
Gate to source charge	Q_{gs}	V_{DD}=40 V, I_D=89 A, V_{GS}=0 to 10 V	-	50	-	nC
Gate to drain charge	Q_{gd}		-	30	-	
Switching charge	Q_{sw}		-	50	-	
Gate charge total	Q_g		-	155	206	
Gate plateau voltage	$V_{plateau}$		-	4.6	-	V
Output charge	Q_{oss}	V_{DD}=40 V, V_{GS}=0 V	-	210	279	nC
Reverse Diode						
Diode continous forward current	I_S	T_C=25 °C	-	-	89	A
Diode pulse current	$I_{S,pulse}$		-	-	356	
Diode forward voltage	V_{SD}	V_{GS}=0 V, I_F=89 A, T_j=25 °C	-	0.9	1.2	V
Reverse recovery time	t_{rr}	V_R=40 V, I_F=I_S, di_F/dt=100 A/µs	-	78	-	ns
Reverse recovery charge	Q_{rr}		-	181	-	nC

[5)] See figure 16 for gate charge parameter definition

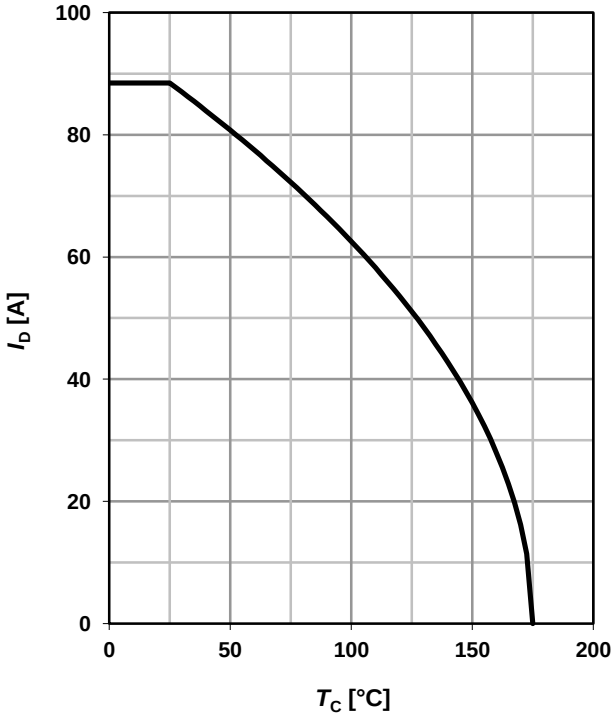
1 Power dissipation

$P_{tot}=f(T_C)$



2 Drain current

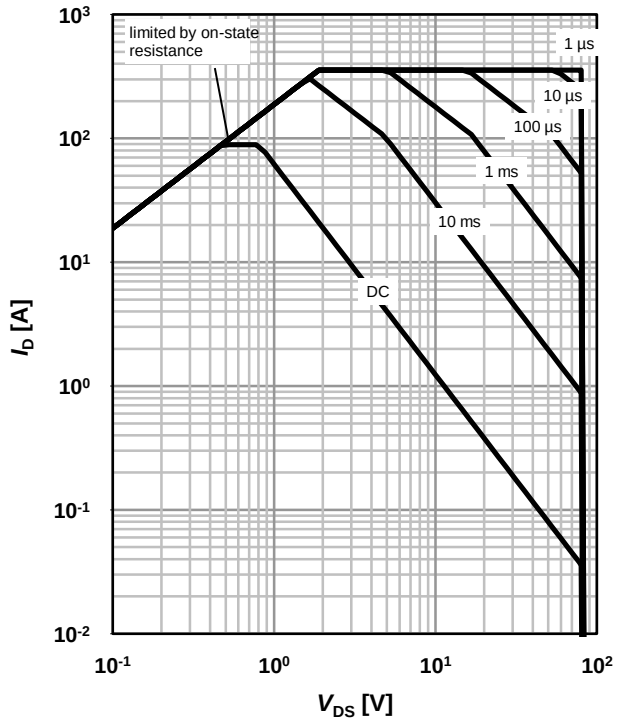
$I_D=f(T_C)$; $V_{GS}\geq 10$ V



3 Safe operating area

$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$

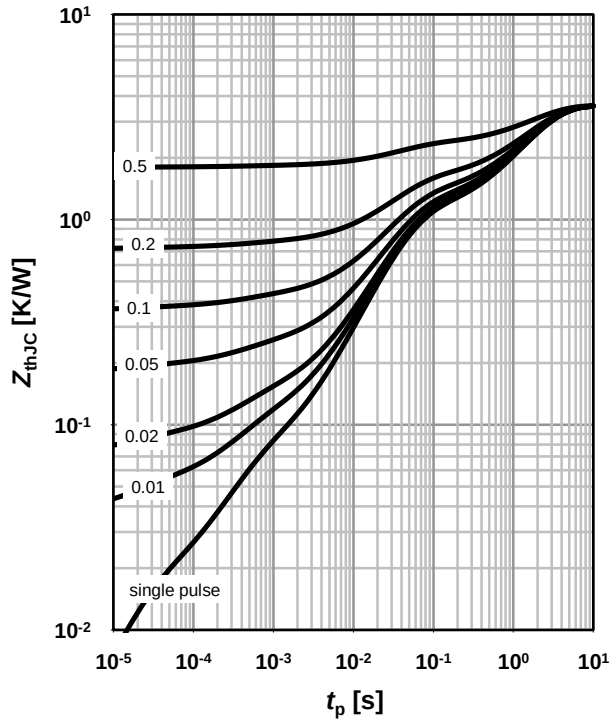
parameter: t_p



4 Max. transient thermal impedance

$Z_{thJC}=f(t_p)$

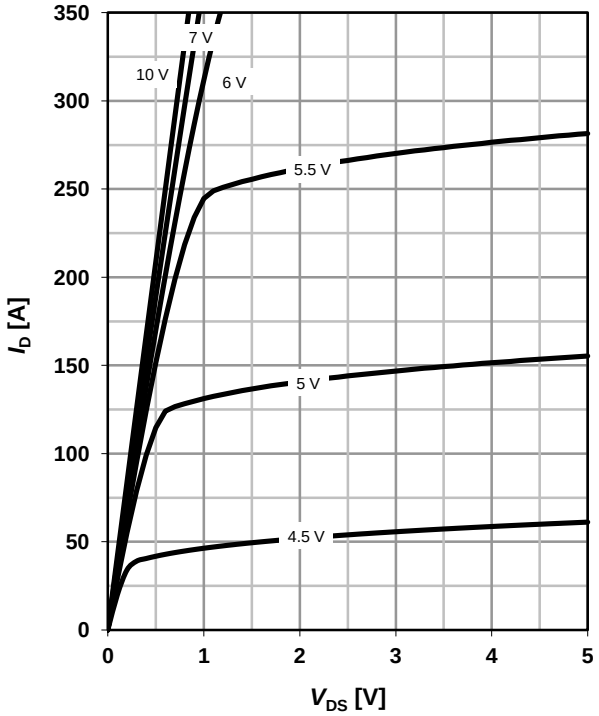
parameter: $D=t_p/T$



5 Typ. output characteristics

$I_D=f(V_{DS})$; T_j=25 °C

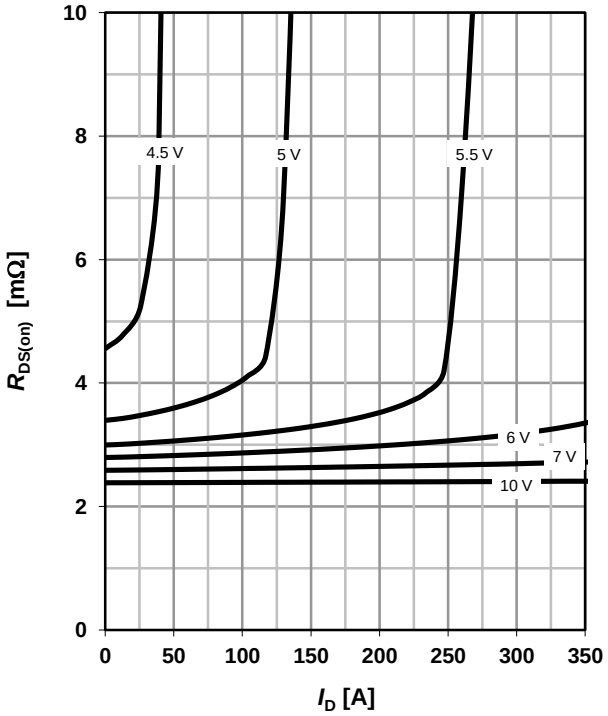
parameter: V_{GS}



6 Typ. drain-source on resistance

$R_{DS(on)}=f(I_D)$; T_j=25 °C

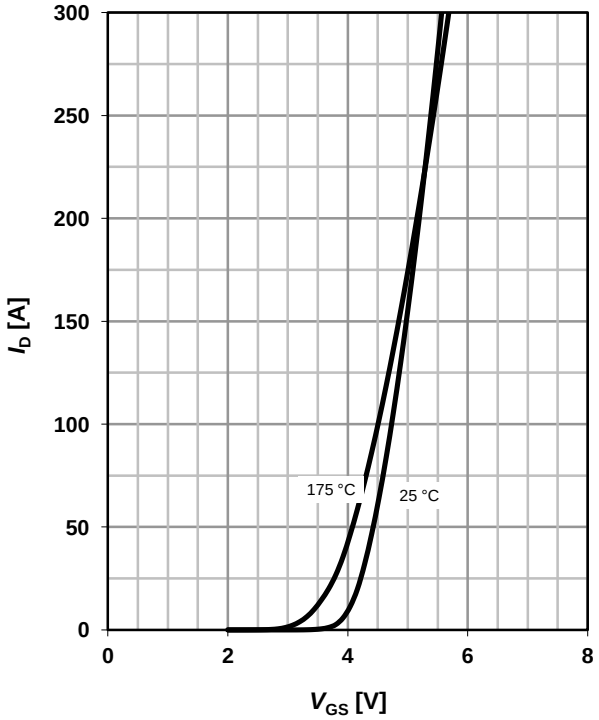
parameter: V_{GS}



7 Typ. transfer characteristics

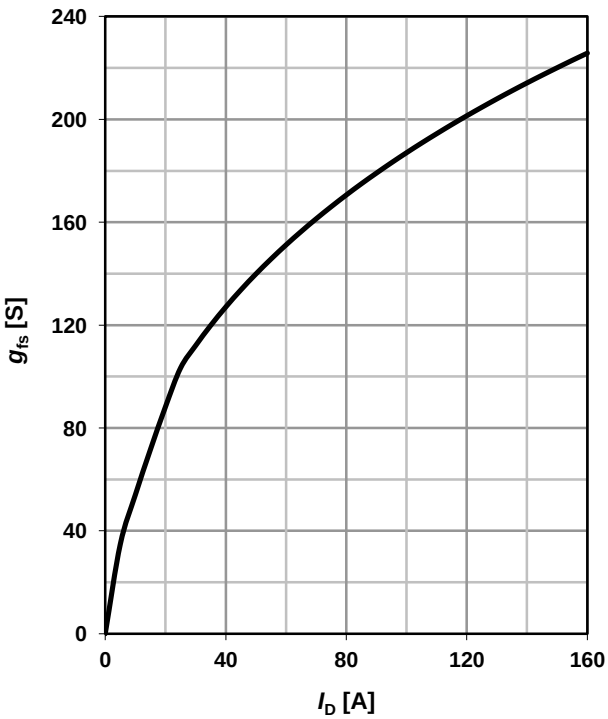
$I_D=f(V_{GS})$; $|V_{DS}|>2|I_D|R_{DS(on)max}$

parameter: T_j



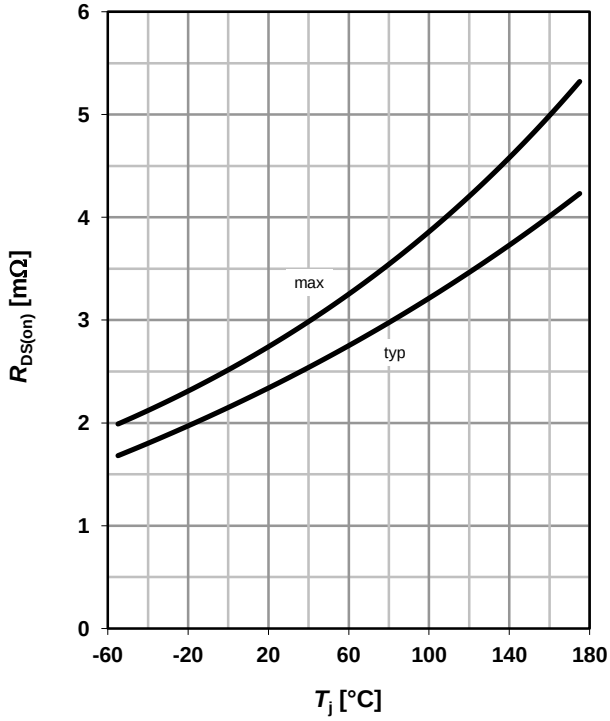
8 Typ. forward transconductance

$g_{fs}=f(I_D)$; T_j=25 °C



9 Drain-source on-state resistance

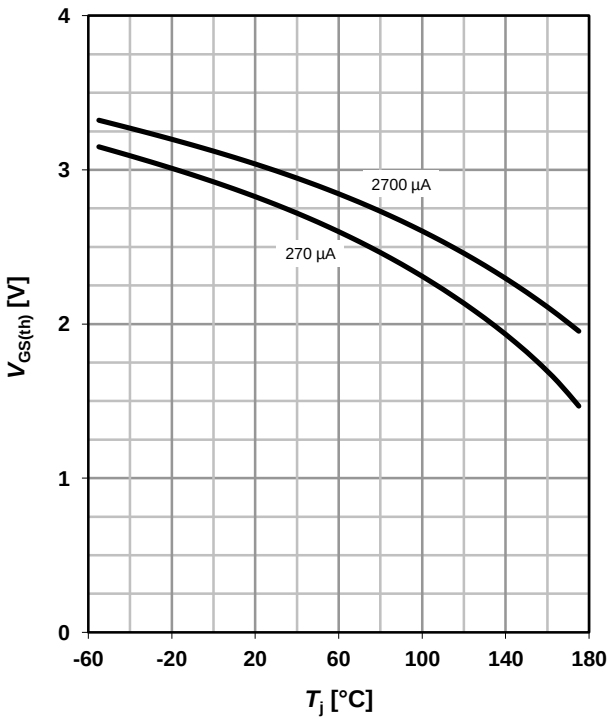
$R_{DS(on)}$=f(T_j); I_D=89 A; V_{GS}=10 V



10 Typ. gate threshold voltage

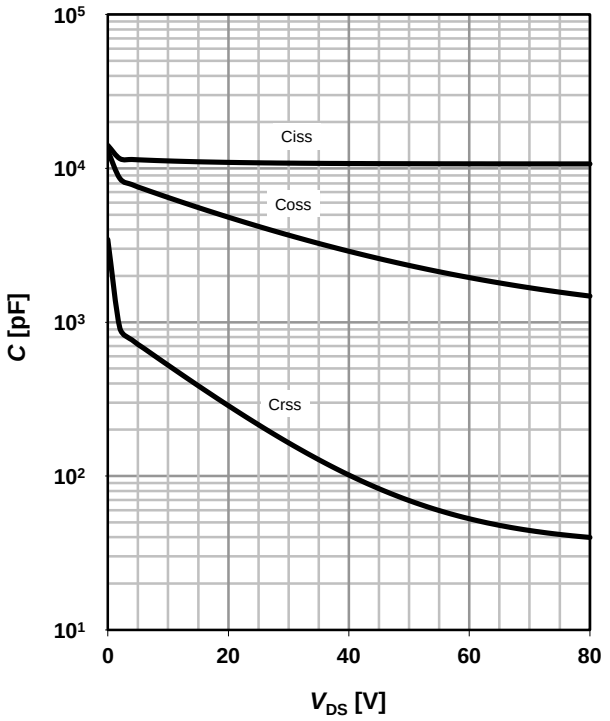
$V_{GS(th)}$=f(T_j); V_{GS}=V_{DS}

parameter: I_D



11 Typ. capacitances

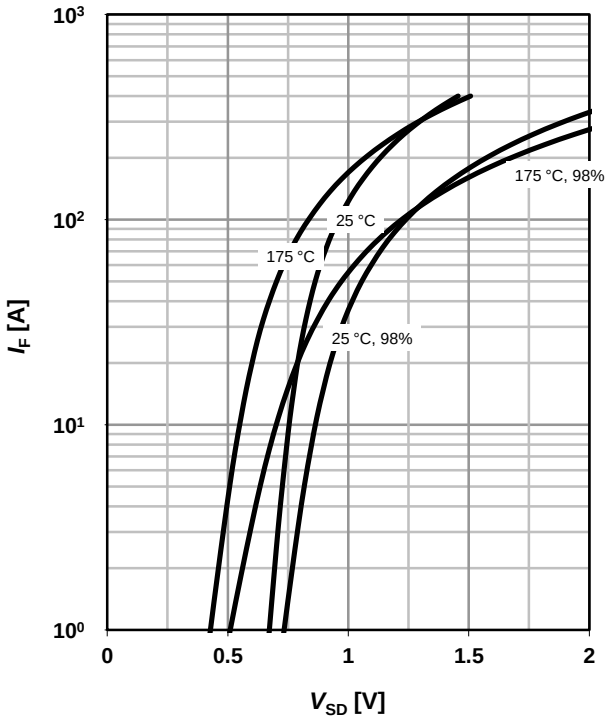
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz



12 Forward characteristics of reverse diode

I_F=f(V_{SD})

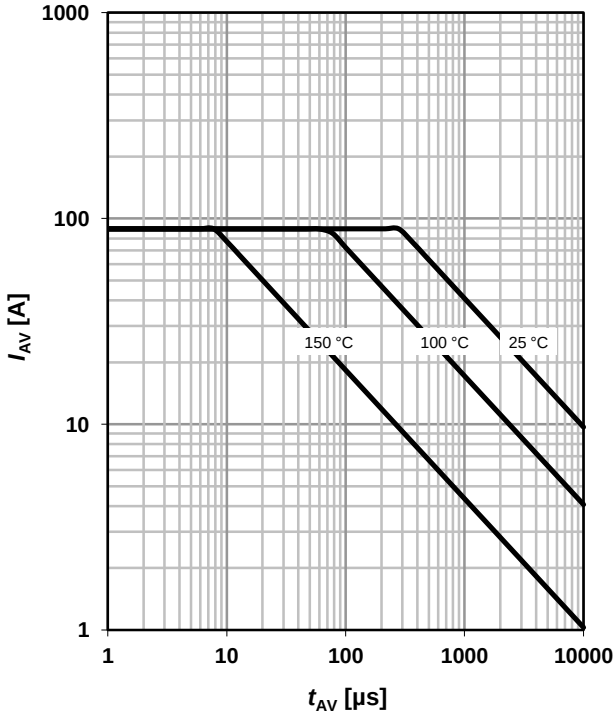
parameter: T_j



13 Avalanche characteristics

I_{AS}=f(t_{AV}); R_{GS}=25 Ω

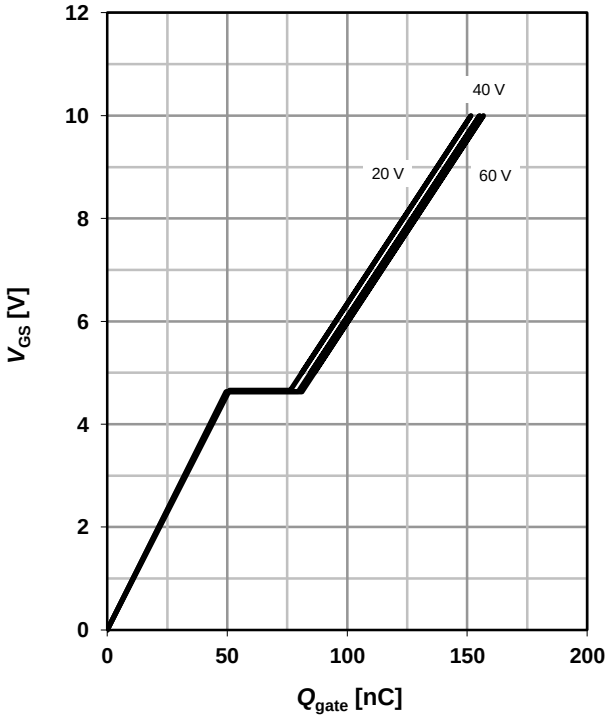
parameter: $T_{j(start)}$



14 Typ. gate charge

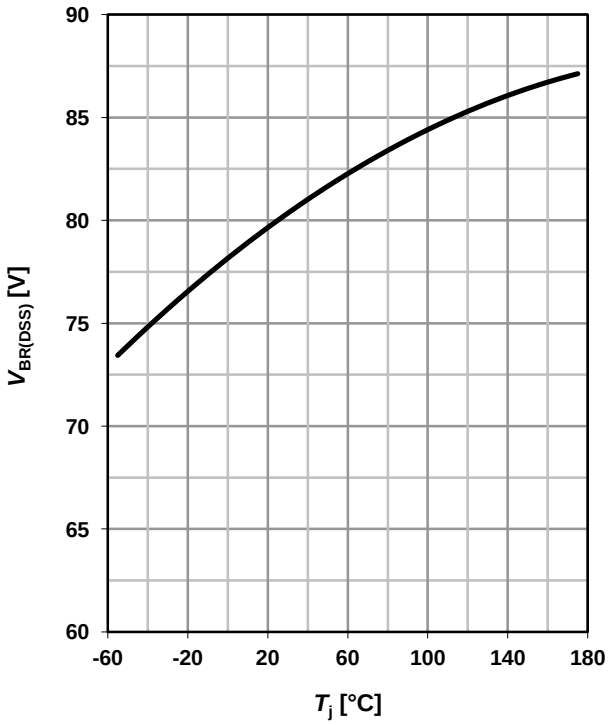
V_{GS}=f(Q_{gate}); I_D=89A pulsed

parameter: V_{DD}

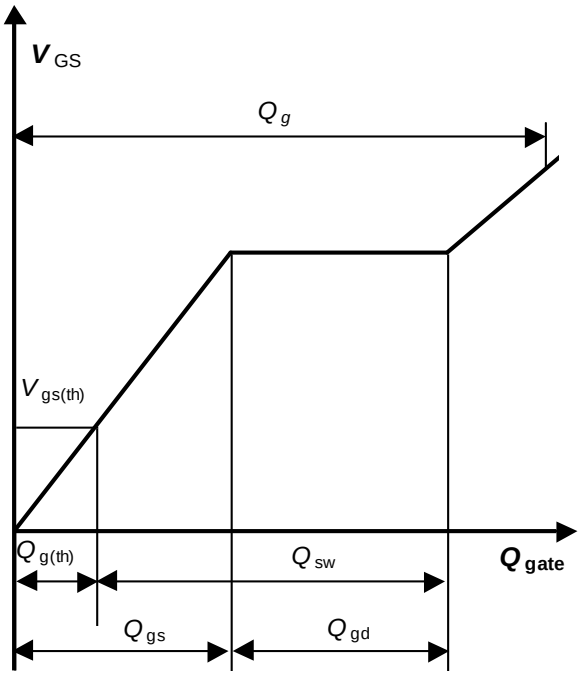


15 Drain-source breakdown voltage

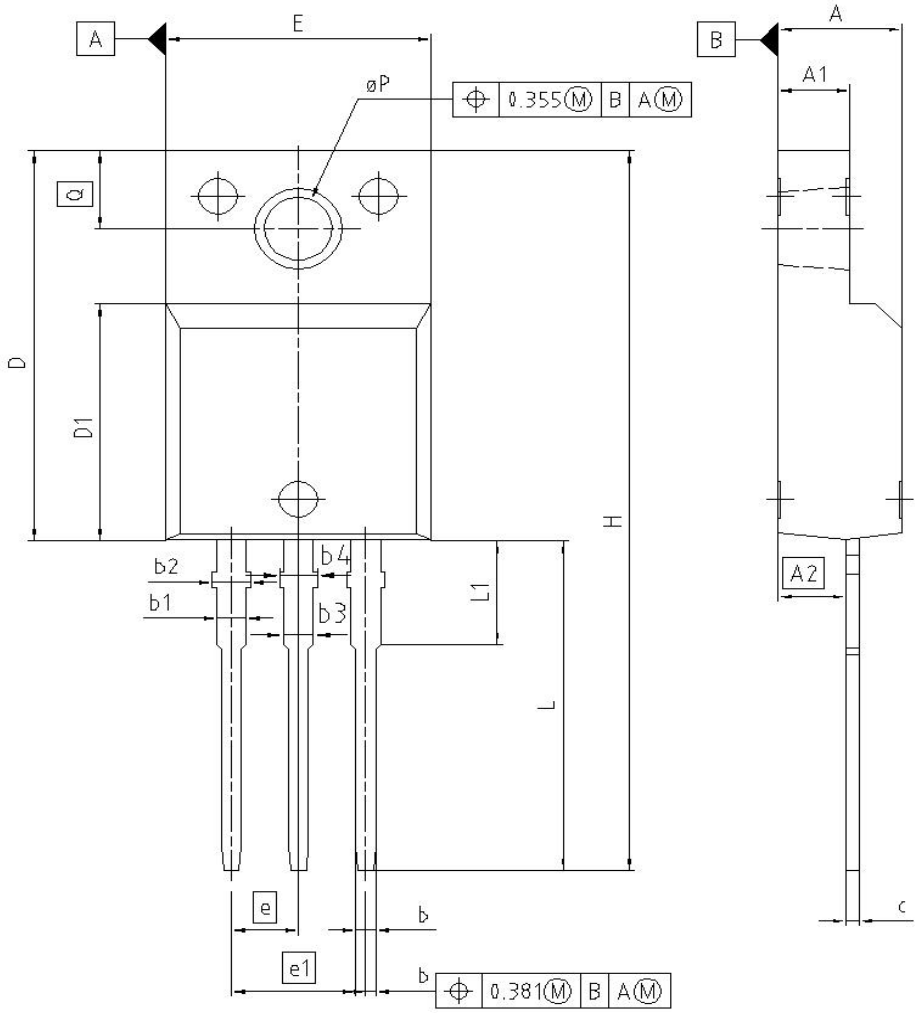
$V_{BR(DSS)}$=f(T_j); I_D=1 mA



16 Gate charge waveforms



PG-TO-220-FP



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.55	4.85	0.179	0.191
A1	2.55	2.85	0.100	0.112
A2	2.42	2.72	0.095	0.107
b	0.65	0.85	0.026	0.033
b1	0.95	1.33	0.037	0.052
b2	0.95	1.51	0.037	0.059
b3	0.65	1.33	0.026	0.052
b4	0.65	1.51	0.026	0.059
c	0.40	0.63	0.016	0.025
D	15.85	16.15	0.624	0.636
D1	9.53	9.83	0.375	0.387
E	10.35	10.65	0.407	0.419
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H	29.45	29.75	1.159	1.171
L	13.45	13.75	0.530	0.541
L1	3.15	3.45	0.124	0.136
øP	2.95	3.20	0.116	0.126
Q	3.15	3.50	0.124	0.138

REFERENCE	../..
SCALE	0, 2.5, 0, 2.5, 5mm
EUROPEAN PROJECTION	
ISSUE DATE	08-01-2007
FILE	TO220_2

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